MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

Monolithic Dual Switching Diodes

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	75	Vdc
D.C. Reverse Voltage MMBD2837LT1G, SMMBD2837LT1G MMBD2838LT1G	V _R	30 50	Vdc
Peak Forward Current	I _{FM}	450 300	mAdc
Average Rectified Current	I _O	150 100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C	P_{D}	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance,	$R_{\theta JA}$		°C/W
Junction-to-Ambient		556	
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
- Canada			
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

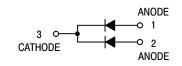


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SOT-23 (TO-236AB) CASE 318 STYLE 9



MARKING DIAGRAM



M = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
Device	1 ackage	Omphing
MMBD2837LT1G	SOT-23	3,000 /
	(Pb-Free)	Tape & Reel
SMMBD2837LT1G	SOT-23	3,000 /
	(Pb-Free)	Tape & Reel
MMBD2838LT1G	SOT-23	3,000 /
	(Pb-Free)	Tape & Reel

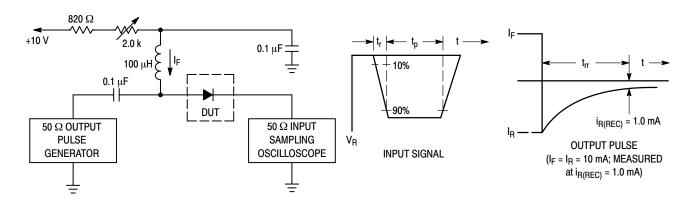
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

ELECTRICAL CHARACTERISTICS (EACH DIODE) (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage (I _(BR) = 100 μAdc) MMBD2837LT1G, SMMBD2837LT1G MMBD2838LT1G	V _(BR)	35 75	_ _	Vdc
Reverse Voltage Leakage Current (Note 3.) (V _R = 30 Vdc) MMBD2837LT1G, SMMBD2837LT1G (V _R = 50 Vdc) MMBD2838LT1G	I _R	-	0.1	μAdc
Diode Capacitance (V _R = 0 V, f = 1.0 MHz)	C _T	-	4.0	pF
Forward Voltage (I _F = 10 mAdc) (I _F = 50 mAdc) (I _F = 100 mAdc)	V _F	- - -	1.0 1.0 1.2	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$, $I_{R(REC)} = 1.0 \text{ mAdc}$) (Figure 1)	t _{rr}	_	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 $k\Omega$ variable resistor adjusted for a Forward Current (IF) of 10 mA.

Notes: 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.

Notes: 3. tp » trr

Figure 1. Recovery Time Equivalent Test Circuit

^{3.} For each individual diode while the second diode is unbiased.

MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

CURVES APPLICABLE TO EACH CATHODE

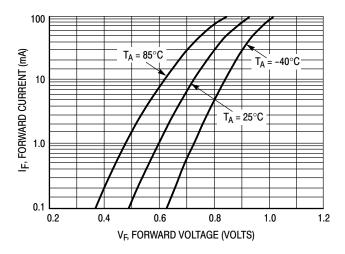


Figure 2. Forward Voltage

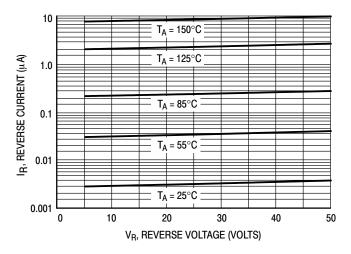


Figure 3. Leakage Current

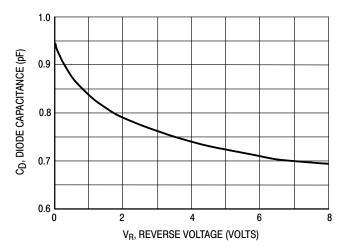


Figure 4. Capacitance

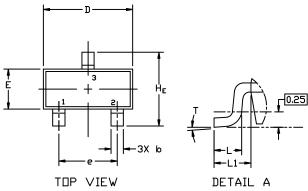




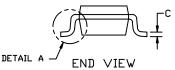
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NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10*



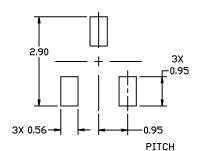


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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